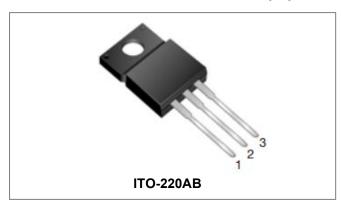






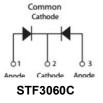
# STF3060C(R) SCHOTTKY RECTIFIER

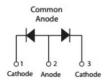


### **Features**

- 150 °C T<sub>J</sub> operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**





STF3060CR

### **Applications**

- · Switching power supply
- Converters
- Free-Wheeling diodes
- · Reverse battery protection

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	60	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=100°C, rectangular wave form	15(Per Leg) 30(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse, Tc=25°C	170	А

## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case(Per Leg)	R <sub>θ</sub> JC	DC operation	6	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

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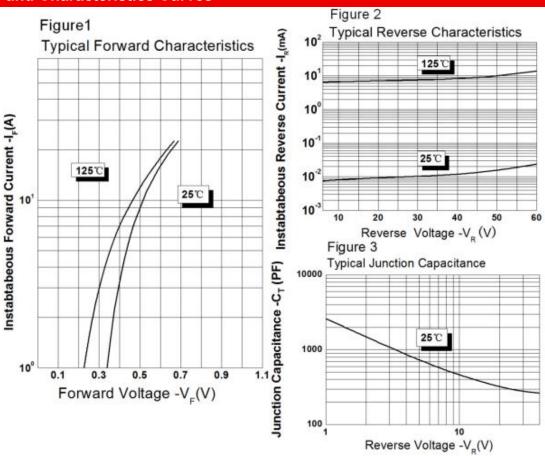


## **Electrical Characteristics:**

Characteristics	Symbol	mbol Condition		Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 5A, Pulse, T <sub>J</sub> = 25°C	0.42	-	
		@ 7.5A, Pulse, T <sub>J</sub> = 25°C	0.48	-	V
		@ 15A, Pulse, T <sub>J</sub> = 25°C	0.59	0.70	
	V <sub>F2</sub>	@ 5A, Pulse, T <sub>J</sub> = 25°C	0.35	-	
		@ 7.5A, Pulse, T <sub>J</sub> =125℃	0.41	-	V
		@ 15A, Pulse, T <sub>J</sub> = 125℃	0.55	0.65	
Reverse Current(Per Leg)*	I <sub>R1</sub>	$@V_R = \text{rated } V_{R,} T_J = 25 ^{\circ} C$	0.03	1.2	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_{R,} T_J = 125^{\circ}C$	14	45	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz$	712	-	pF
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T <sub>A</sub> = 25 °C)		Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	
	V <sub>ISO</sub>	Clip mounting, the epoxy body is inside the heatsink.	-	3500	V
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

## **Ratings and Characteristics Curves**



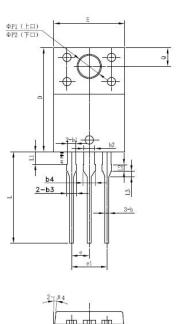
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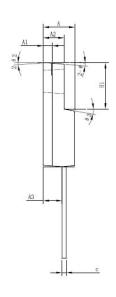






### **Mechanical Dimensions ITO-220AB**







0)/4504	Millimeters		
SYMBOL	MIN.	TYP.	MAX.
Α	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
С	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
е		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦΡ1( ├ □ )	3.30	3.50	3.70
<b>ΦP2</b> (下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

## **Marking Diagram**





#### Where XXXXX is YYWWL

= Device Type = Package type 30 = Forward Current (30A) = Reverse Voltage (60V) 60 = Configuration = SSG C(R) SŠĞ = Year YY = Week WW

= Lot Number Cautions: Molding resin

Epoxy resin UL:94V-0

## **Tube Specification**



## **Ordering Information**

Device	Package	Shipping
STF3060C(R)	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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